

# M64897GP

PLL Frequency Synthesizer with DC/DC Converter for PC

REJ03F0167-0200 Rev.2.00 Jun 14, 2006

### Description

The M64897GP is a semiconductor integrated circuit consisting of PLL frequency synthesizer for TV/VCR/PC using  $I^2C$  BUS control. It contains the prescaler with operating up to 1.3 GHz, 4 band drivers and DC/DC converter for Tuning voltage.

# Features

- Built-in DC/DC converter for Tuning voltage
- 4 integrated PNP band drivers ( $I_0 = 30 \text{ mA}$ ,  $V_{\text{sat}} = 0.2 \text{ V Typ.} @V_{\text{CC1}} \text{ to } 10 \text{ V}$ )
- Built-in prescaler with input amplifier (f max = 1.3 GHz)
- PLL lock/unlock status display out put (Built-in pull up resistor)
- X'tal 4 MHz is used to realize 3 type of tuning steps (Divider ratio 1/512, 1/640, 1/1024)
- Software compatible with M64894
- Built-in Power on reset system
- Small Package (SSOP)

# Application

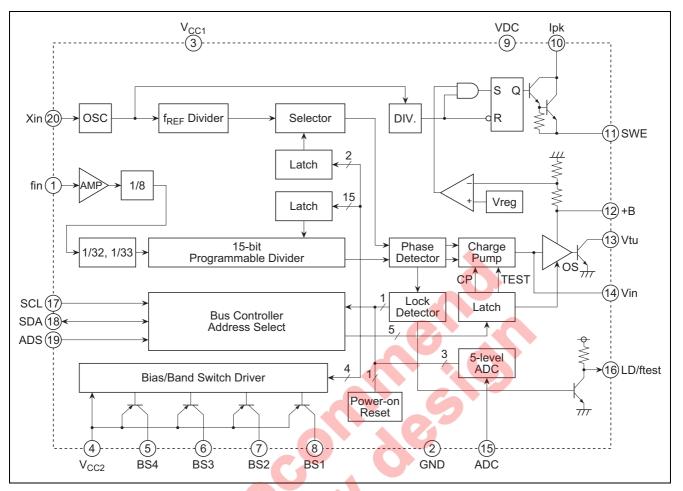
PC, TV, VCR tuners

# **Recommended Operating Condition**

- Supply voltage range
  - V<sub>CC1</sub> = 4.5 to 5.5 V
  - -- V<sub>CC2</sub> = V<sub>CC1</sub> to 10 V
- Rated supply voltage
- -- V<sub>CC1</sub> = 5 V
- $--V_{\rm CC2} = V_{\rm CC1}$



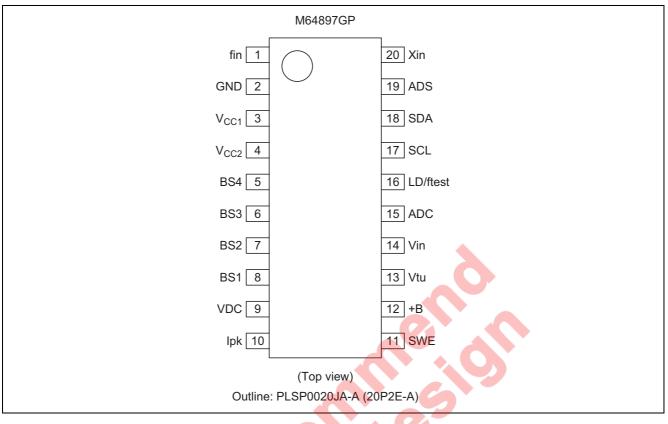
# **Block Diagram**



North



# **Pin Arrangement**







# **Pin Description**

Pin	Cumb al	Din nome	Function
<b>No.</b>	Symbol fin	Pin name Prescaler input	Function Input for the VCO frequency.
2	GND	GND	Ground to 0 V.
2		Power supply voltage 1	
	V <sub>CC1</sub>		Power supply voltage terminal.5.0 V $\pm$ 0.5 V
4	V <sub>CC2</sub>	Power supply voltage 2	Power supply for band switching, V <sub>CC1</sub> to 10 V
5	BS4	Band switching outputs	PNP open collector method is used. When the band switching data is "H", the output is ON.
6	BS3		When it is "L", the output is OFF.
7	BS2		
8	BS1	20/20	
9	VDC	DC/DC power supply voltage	DC/DC power supply voltage terminal.5.0 V $\pm$ 0.5 V
10	lpk	Peak current detect	When potential difference with VDC terminal becomes more than 0.33 V by current limiting detector of DC/DC converter, the listing rises with off.
11	SWE	Switching output	DC/DC converter oscillator output.
12	+B	Power supply voltage	Power supply voltage for tuning voltage.
13	Vtu	Tuning output	This supplies the tuning voltage.
14	Vin	Filter input (Charge pump output)	This is the output terminal for the LPF input and charge pump output. When the phase of the programmable divider output (f 1/N) is ahead compared to the reference frequency ( $f_{REF}$ ), the "source" current state becomes active. If it is behind, the "sink" current becomes active. If the phases are the same, the high impedance state becomes active.
15	LD/ftest	Lock detect/Test port	Lock detector output. When loop of phase locked loop locked it, it rises with "H" level in "L" level or unlock. In control byte data input, the programmable freq. divider output and reference freq. output is selected by the test mode.
16	ADC	AD converter input	A/D conversion of the input voltage.
17	SCL	Clock input	Data is read into the shift register when the clock signal falls
18	SDA	Data input	Input for band SW and programmable freq. divider set up. In lead mode, it outputs lock detector output and power down flag and a state of 5 level A/D converter.
19	ADS	Address switching input	Chip address sets it up with the input condition of terminal.
20	Xin	This is connected to the crystal oscillator	4.0 MHz crystal oscillator is connected.



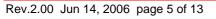
# **Absolute Maximum Ratings**

			$(Ta = -20^{\circ}C to$	+75°C, unless otherwise noted)
ltem	Symbol	Ratings	Unit	Condition
Supply Voltage 1	V <sub>CC1</sub>	6.0	V	Pin 3
Supply voltage 2	V <sub>CC2</sub>	10.8	V	Pin 4
Input voltage	VI	6.0	V	Not to exceed V <sub>CC1</sub>
Output voltage	Vo	6.0	V	f <sub>REF</sub> output
Voltage applied when the band output is OFF	VBSOFF	10.8	V	
Band output current	I <sub>BSON</sub>	40.0	mA	Per 1 band output circuit
ON the time when the band output is ON	t <sub>BSON</sub>	10	S	40 mA per 1 band output circuit 3 circuits are pn at same time.
Power dissipation	Pd	255	mW	Ta = 75°C
Operating temperature	Topr	-20 to +75	°C	
Storage temperature	Tstg	-40 to +125	°C	

# **Recommended Operating Conditions**

Symbol Ratings Unit Conditions ltem 4.5 to 5.5 Supply voltage 1 V V<sub>CC1</sub> Pin 3 V Supply voltage 2 V<sub>CC2</sub>  $V_{\text{CC1}}$  to 10.0 Pin 4 Operating frequency (1) 4.0 V Crystal oscillation circuit f<sub>opr1</sub> Operating frequency (2) 80 to 1300 MHz f<sub>opr2</sub> Band output current 5 to 8 0 to 30 Normally 1 circuit is on. 2 circuits on at the  $I_{BDL}$ mΑ same time is max. It is prohibited to have 3 or more circuits turned on at the same time.

(Ta =  $-20^{\circ}$ C to  $+75^{\circ}$ C, unless otherwise noted)





# **Electrical Characteristics**

			Test		Limits			
Item		Symbol	Pin	Min.	Тур.	Max.	Unit	Test Conditions
Input termina	"H" input voltage	V <sub>IH</sub>	17 to 18	3.0	_	V <sub>CC1</sub> + 0.3	V	
ls	"L" input voltage	VIL	17 to 18		_	1.5	V	
	"H" input current	IIH	17 to 18	_	_	10	μA	$V_{CC1} = 5.5V, Vi = 4.0V$
	"L" input current	l <sub>IL</sub>	17, 18	_	-4/-14	-10/-30	μA	$V_{CC1} = 5.5V, Vi = 0.4V$
SDA	"L" output voltage	Vol	18	_	_	0.4	μA	$V_{CC1} = 5.5V, I_C = 3mA$
output	Leak current	ILO	18	_	_	10	μA	$V_{CC1} = 5.5V, V_0 = 5.5V$
Lock output	"H" output voltage	V <sub>OH</sub>	16	5.0	_	_	V	$V_{CC1} = 5.5V$
	"L" output voltage	V <sub>OL</sub>	16	—	0.3	0.5	V	$V_{CC1} = 5.5V$
Band	Output voltage	V <sub>BS</sub>	5 to 8	11.6	11.8	_	V	$V_{CC2} = 9V, I_0 = -30mA$
SW	Leak current	I <sub>olk1</sub>	5 to 8	_	_	-10	μΑ	$V_{CC2} = 9V,$ Band SW is OFF $V_0 = 0V$
Tuning output	Output voltage "H"	V <sub>toH</sub>	13	30.5	—		V	+B = 31V
	Output voltage "L"	V <sub>toL</sub>	13	_	0.2	0.4	V	+B = 31V
Charge pump	"H" output current	I <sub>CPO</sub>	14	-	270	370	μA	$V_{CC1} = 5.0V, V_0 = 2.5V$
	Leakage current	I <sub>CPLK</sub>	14		<u> </u>	50	nA	$V_{CC1} = 5.0V, V_0 = 2.5V$
Supply c	urrent 1	I <sub>CC1</sub>	3		20	30	mA	$V_{CC1} = 5.5V$
Supply	4 circuits OFF	I <sub>CC2A</sub>	4			0.3	mA	$V_{CC2} = 9V$
current 2	1 circuits ON, Output open	I <sub>CC2B</sub>	4	-	4.0	6.0	mA	$V_{CC2} = 9V$
	Output current 30 mA	I <sub>CC2C</sub>	4		34.0	36.0	mA	$V_{CC2} = 9V, I_0 = -30mA$
DC/DC C	Converter						•	
Supply c	urrent (action)	I <sub>CCdc</sub>	9	—	1.3	3.0	mA	$V_{CC1} = 5.5V$
Output v	oltage 🛛 🔺	Vdo	12	28	31	35	V	$V_{CC1} = 5.5V$
OSC free	quency	fosc	11	—	571	_	kHz	$V_{CC1} = 5.5V$
Current I	imit detect voltage	Vipk	10	—	330	_	mV	$V_{CC1} = 5.5V$
Jote T	he typical values are	at Vcci = 5	V Voor	- 9 0 V T	a – +25°C			•

 $(Ta = -20^{\circ}C \text{ to } +75^{\circ}C, \text{ unless otherwise noted}, V_{CC1} = 5.0 \text{ V}, V_{CC2} = 9.0 \text{ V})$ 

Note: The typical values are at  $V_{CC1} = 5.0$  V,  $V_{CC2} = 9.0$  V, Ta = +25°C.

# **Switching Characteristics**

 $(Ta = -20^{\circ}C \text{ to } +75^{\circ}C, \text{ unless otherwise noted}, V_{CC1} = 5.0 \text{ V}, V_{CC2} = 9.0 \text{ V})$ 

Rev.2.00 Jun 14, 2006 page 7 of 13



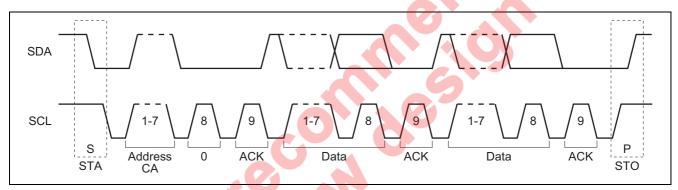
# Method of Setting Data

The input information to consist of 2 or data of 4 bytes to lead to chip address is received in  $I^2C$  bus receiver. It shows a definition of bus protocol admitted in the following.

1_STA	CA	CB	BB	STO				
2_STA	CA	D1	D2	STO				
3_STA	CA	CB	BB	D1	D2	STO		
4_STA	CA	D1	D2	CB	BB	STO		
STA : Start c	condition	ı						
STO : Stop c	ondition	ı						
CA : Chip a	address							
CB : Contro	ol data b	yte						
BB : Band	3 : Band SW data byte							
D1 : Divide	: Divider data byte							
D2 : Divide	: Divider data byte							

The information of 5 bytes necessary for circuit operation is chip address and control data, band SW data of 2 bytes and divider byte of 2 bytes. After the chip address input, 2 or data of 4 bytes are received.

Function bit is contained the first and the third data byte to distinguish between divider data and control data, band data, and "0" goes ahead of divider data, and "1" goes ahead of control data, band SW data.



#### Write Mode Format

Byte	MSB								LSB
Address byte	1	1	0	0	0	MA1	MA0	0	А
Divider byte 1	0	N14	N13	N12	N11	N10	N9	N8	А
Divider byte 2	N7	N6	N5	N4	N3	N2	N1	N0	А
Control byte 1	1	Х	T2	T1	Т0	RSa	RSb	OS	А
Band SW byte	X	Х	Х	Х	BS4	BS3	BS2	BS1	А

#### **Read Mode Format**

Byte	MSB								LSB
Address byte	1	1	0	0	0	MA1	MA0	1	А
Status byte 1	POR	FL	Х	Х	Х	A2	A1	A0	А



# Data Cording Example

### Write Mode Format Example

Byte	MSB								LSB	Condotion in Data Setting
Address byte	1	1	0	0	0	1	1	0	1	ADS input V <sub>CC1</sub>
Divider byte 1	0	1	0	0	0	0	0	0	1	Divider ratio N = 16544
Divider byte 2	1	0	1	0	0	0	0	0	1	
Control byte 1	1	1	0	0	0	0	1	0	1	f <sub>REF</sub> divider ratio 1/1024
Band SW byte	0	0	0	0	1	0	0	0	1	BS4 output ON

Note:  $f_{VCO} = N \bullet 8 \bullet f_{REF} = 16544 \bullet 8 \bullet (4 \text{ MHz}/1024) = 517 \text{ MHz}$ 

### Read Mode Format Example (Loop locked)

Byte	MSB								LSB	Condotion in Data Setting
Address byte	1	1	0	0	0	1	1	1	1	ADS Applied voltage
										0.9 V <sub>CC1</sub> to V <sub>CC1</sub>
Status byte	0	1	1	1	1	0	1	1	1	ADS Applied voltage
										0.45 V <sub>CC1</sub> to 0.6 V <sub>CC1</sub>

Use data input for "1" so that the data of Read mode and Write mode return ACK signal "0" to micro computer in 9 bits of each byte.

# Test Mode Data Set Up Method

### Test Mode Bit Set Up

- X : Random, 0 or 1. normal "0"
- MA1, MA0 : Programmable address bit

Address Input Voltage	MA1	MA0
0 to 0.1 V <sub>CC1</sub>	0	0
Always valid	0	1
0.4 V <sub>CC1</sub> to 0.6 V <sub>CC1</sub>	1	0
0.9 V <sub>CC1</sub> to V <sub>CC1</sub>	1	1

Note: N14 to N0: How to set dividing ratio of the programmable the divider

Dividing ratio = N14 
$$(2^{14} = 16384) + +N0 (2^{0} = 1)$$

Therefore, the range of divider N is 1,024 to 32,768

Example)  $f_{VCO} = f_{REF} \bullet 8 \bullet N$ 

= 3.90625 • 8 • N

### T2, T1, T0: Setting Up for The Test Mode

T2	T1	Т0	Charge Pump	Pin 12 Condition	Mode
0	0	Х	Normal operation	ADC input	Normal operation
0	1	Х	High impedance	ADC input	Test mode
1	1	0	Sink	ADC input	Test mode
1	1	1	Source	ADC input	Test mode
1	0	0	High impedance	f <sub>REF</sub> output	Test mode
1	0	1	High impedance	f1/N output	Test mode



### RSa, RSb: Set Up for The Reference Frequency Divider Ratio

RSa	RSb	Divider Ratio
1	1	1/512
0	1	1/1024
X	0	1/640

### **OS: Set Up The Tuning Amplifier**

OS	Tuning Voltage Output	Mode
0	ON	Normal
1	OFF	Test

POR : Power on reset flag. "1" output at reset

FL : Lock detector flag. "1" output at locked, "0" output at unlocked

### A2, A1, A0: 5 Level A/D Converter Output Data

	ADC Input Voltage	A2	A1	A0
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$0.6\pm V_{CC1}$ to $V_{CC1}$	1	0	0
$0.15 \pm V_{CC1} \text{ to } 0.3 \pm V_{CC1} \qquad 0 \qquad 1$	$0.45\pm V_{CC1}$ to $0.6\pm V_{CC1}$	0	1	1
	$0.3\pm V_{CC1}$ to $0.45\pm V_{CC1}$	0		0
	$0.15\pm V_{CC1}$ to $0.3\pm V_{CC1}$	0	0	1
	0 to 0.15 $\pm$ V_{CC1}	0	0	0

Note: The voltage accuracy allowance range:  $0.03 \pm V_{CC1}$  (V)

# **Power on Reset Operation**

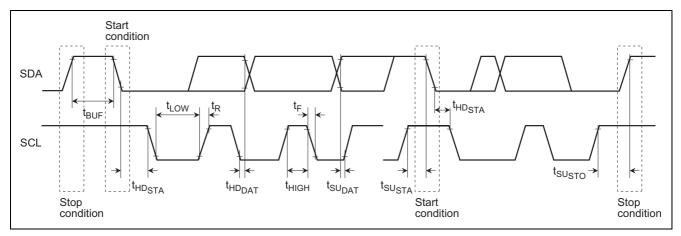
(Initial state the power is turned ON)

	0 20				
ower on Reset Operation					
nitial state the power is turn	ned ON)				
BS4 to BS1	: OFF				
Charge pump	: High impedance				
Tuning amplifier	: OFF				
Charge pump current	: 270 µA				
Frequency division ratio	: 1/1024				
Lock detect	: H				

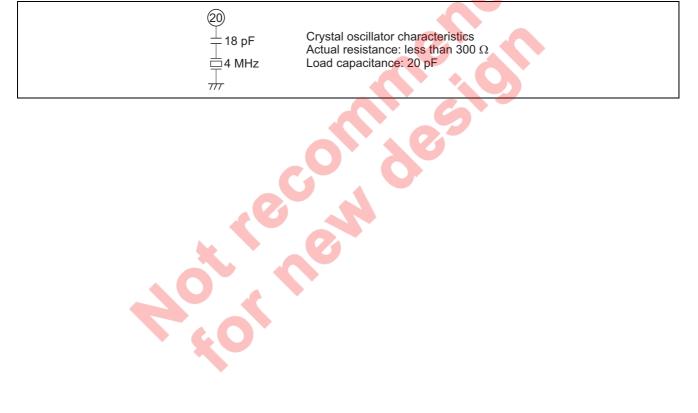
Charge pump current is replaced by  $70 \,\mu\text{A}$  when locks it by automatic change facility.



# **Timing Diagram**

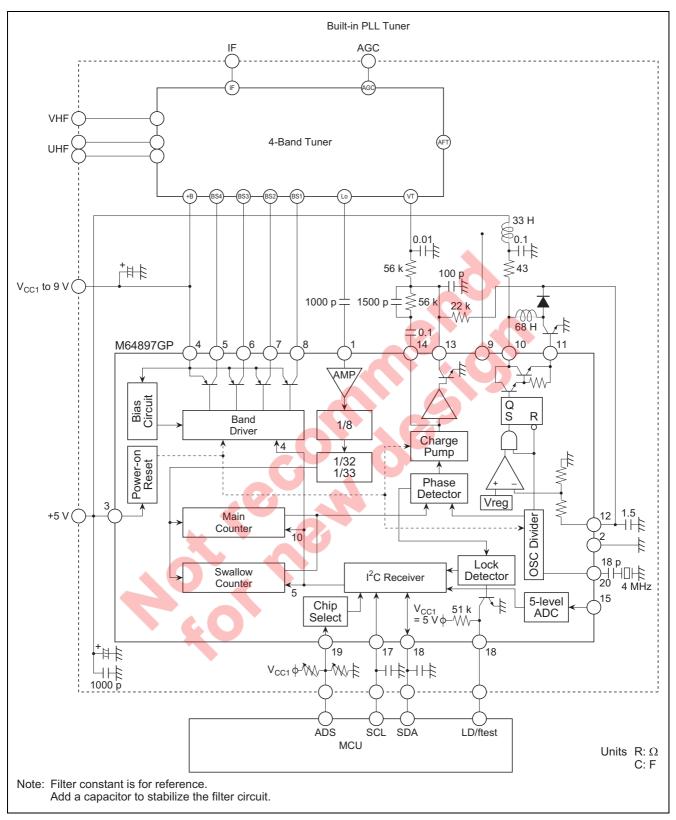


# **Crystal Oscillator Connection Diagram**



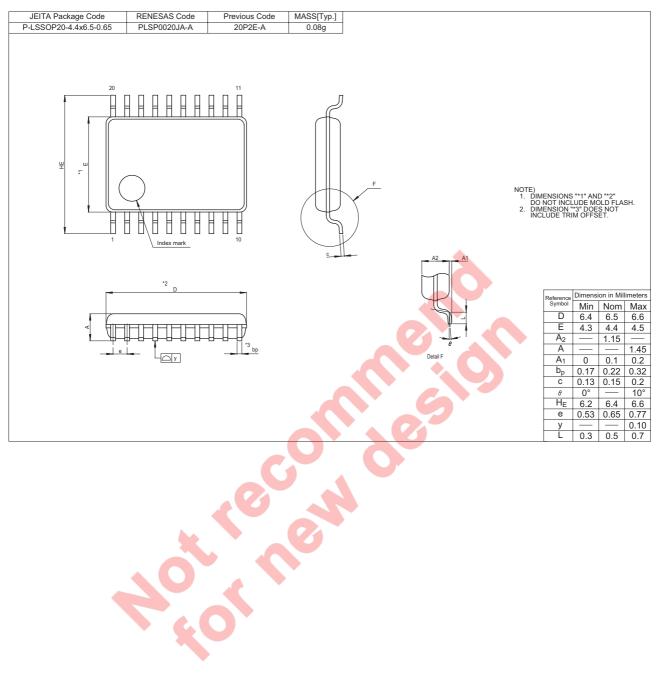


# **Application Example**





# **Package Dimensions**





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Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

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Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510